Supporting Information

Dye Sensitized Nanostructured Crystalline Mesoporous

Tin-doped Indium Oxide Films with Tunable Thickness

for Photoelectrochemical Applications

W. Hamd,¹ M. Chavarot-Kerlidou,^{*,2} J. Fize,² G. Muller,¹ A. Leyris,³ M. Matheron,³ E. Courtin¹, M. Fontecave,^{2,4} C. Sanchez,^{1,4} V. Artero,² and C. Laberty-Robert^{*,1}

1. Laboratoire de Chimie de la Matière Condensée de Paris-UMR7574, CNRS, Université Paris 6, Collège de France, 11 place Marcelin Berthelot 75005 Paris

2. Laboratoire de Chimie et Biologie des Métaux, Université Grenoble 1, CNRS, CEA, 17 rue des Martyrs 38054 Grenoble cedex 9

3. Department of Technology for Biology and Health, CEA LETI-MINATEC, 17 rue des Martyrs, F-38054 Grenoble CEDEX 9, France

4. Collège de France, 11 Place Marcelin Berthelot, 75005 Paris



Figure S1. X-Ray diffraction patterns (a) and FE-SEM images (b) of *templated nano-ITO* films before thermal treatment.



Figure S2. FE-SEM images of *templated nano-ITO* films treated at various temperatures a) 300°C, b) 450°C, c) 550°C in air



Figure S3. EDX (a) and XPS (b) analyses for templated nano-ITO films heat-treated at 450°C in air



Figure S4. Small–angle X–ray diffraction of *templated nano*–ITO films calcined at 450°C. The most intense peak can be attributed to the (220) of mesopores organized into a cubic structure. The peaks before are due to interference.

Table 1. Crystallites size as function of the heat-treatement. Evolution of the crystallites size as function of the heat-treatment, determined from Debye and Scherrer formula (noted D(222)) sherrer in the table), Dmean corresponds to mean diameter obtained by this method, and from Williamson et al. approach (noted D Williamson et hall in Table 1).

Temperature	D (222)-Scherrer	D mean	D williamson et Hall
300 °C	15 nm	15,6 nm	16,6 nm
450 °C	21 nm	20,4 nm	25 nm
550 °C	23 nm	21,5 nm	30 nm





Figure S5. *Top* Cyclic voltammograms of $[Ru(bpy)_3]Cl_2$, 1 mM in 0.1M aqueous HOTf at scan rates varying from 10 to 100 mV.s⁻¹, recorded at a non-functionalized nanostructured ITO electrode (10 layers, treated at 450°C for 1 hour in air; electrode surface: 1 cm²). *Bottom* Linear evolution with the square root of the scan rate of the cathodic and anodic peak currents (capacitive current substracted) related to the Ru^{III}/Ru^{II} couple.



Figure S6. Dependence of the grafting density on the number of layers for multi-layered nanostructured ITO films.





Figure S7. *Top* Cyclic voltammograms of complex 1 adsorbed on planar ITO (electrode surface: 1 cm^2), recorded in 0.1M aqueous HOTf at scan rates varying from 50 to 2000 mV.s⁻¹. *Bottom* Linear evolution with the scan rate of the cathodic and anodic peak currents related to the Ru^{III}/Ru^{II} couple.



Figure S8. Absorption spectrum of complex 1 adsorbed on *templated nano-ITO* (10 layers, treated at 450°C for 1 hour in air), after substraction of the absorption of the non-functionalized *templated nano-ITO* film.



Figure S9. Transmittance for the 10-layers dense nano-ITO film heat-treated at 450°C for 1 h in air



Figure S10. FE-SEM image (cross section view) of a 10 layers dense nano-ITO film treated at 450°C, in air.



Figure S11. *Top* Cyclic voltammograms of complex 1 adsorbed on *dense nano-ITO* (10 layers prepared in the absence of template, treated at 450°C for 1 hour in air; electrode surface: 1 cm²), recorded in 0.1M aqueous HOTf at scan rates varying from 10 to 100 mV.s⁻¹. *Bottom* Linear evolution with the scan rate of the cathodic and anodic peak currents related to the Ru^{III}/Ru^{II} couple.



Figure S12. In situ electrical conductivity of films (thickness = 470 nm) heat-treated in air at 450°C: Evolution of the conductivity as a function of time for 10–layer *templated nano–ITO* films heated in 5% of H_2 in Ar at 200°C.



Figure S13. *Top* Cyclic voltammograms of complex **1** adsorbed on H₂-treated *templated nano-ITO* (10 layers, treated at 450°C for 1 hour in air then under 5% H₂ in Ar at 200°C for 30 min; electrode surface: 1 cm^2), recorded in 0.1M aqueous HOTf at scan rates varying from 10 to 100 mV.s⁻¹. *Bottom* Linear evolution with the scan rate of the cathodic and anodic peak currents related to the Ru^{III}/Ru^{II} couple.



Figure S14. Sections of the cyclic voltammograms of non-functionalized A) 10-layer *templated nano-ITO*, **B**) 10-layer *dense nano-ITO*; **C**) 10 layers H₂-treated *templated nano-ITO*; recorded in 0.1M aqueous HOTf at scan rates varying from 10 to 100 mV.s⁻¹ (electrode surface: 1 cm²).



Figure S15. Peak-to-peak splitting between the oxidation and the reduction peak of complex 1 grafted on a 10-layer *templated nano-ITO* electrode (\blacklozenge), a 10-layer H₂-treated *templated nano-ITO* electrode (\blacktriangle), a 10-layer dense *nano-ITO* electrode (\blacksquare) or a planar ITO electrode (\blacklozenge) (recorded in 0.1M aqueous HOTf at scan rates varying from 10 to 100 mV.s⁻¹).